

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	601	(29/25.41).CCLS.	USPAT; USOCR	OR	OFF	2006/02/27 17:25
S2	110	(29/25.41).cor.	USPAT; USOCR	ADJ	ON	2006/02/27 15:51
S3	536	(438/386).CCLS.	USPAT; USOCR	OR	OFF	2006/02/27 15:51
S5	1	("4829277").PN.	USPAT; USOCR	OR	OFF	2006/02/27 17:29
S6	8	("4538130").PN. OR ("4829277").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2006/02/27 17:29
S7	19	("4614930" "4758813" "4829277" "4835506" "4837542" "4839059" "4862128" "4999600" "5103200" "5216400" "5216401" "5300910" "H000591").PN. OR ("5396209").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2006/02/27 17:32
S8	1045	(438/240).CCLS.	USPAT; USOCR	OR	OFF	2006/02/28 11:03
S9	4	((("6309922") or ("6274502") or ("6258652") or ("6054329")).PN.	USPAT; USOCR	OR	OFF	2006/02/28 10:34
S10	131	(kai and shao or chit and ng or purakh and verma or jia and zheng or sanford and chu).in.	USPAT; USOCR	ADJ	ON	2006/02/28 10:36
S11	209	(kai and shao or chit and ng or purakh and verma or jia and zheng or sanford and chu).in.	US-PGPUB; USPAT; USOCR	ADJ	ON	2006/02/28 10:36
S12	0	("2005/0086780").URPN.	USPAT	ADJ	ON	2006/02/28 10:59
S15	151	S8 and (low-k or high-k or "high k" or "low k")	USPAT; USOCR	ADJ	ON	2006/02/28 11:03
S16	151	S8 and (low-k or high-k or "high k" or "low k")	US-PGPUB; USPAT; USOCR	ADJ	ON	2006/02/28 11:03
S17	1424	(438/240).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/28 11:58
S18	230	S17 and (low-k or high-k or "high k" or "low k")	US-PGPUB; USPAT; USOCR	ADJ	ON	2006/02/28 11:04

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S19	15	("5583359" "5696394" "5700731" "5895239" "5926359" "5939766" "6177305" "6180976" "6200629" "6232197" "6238964" "6251740" "6259128" "6385033" "6479850").PN. OR ("6717193").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2006/02/28 11:47
S20	86	(438/957).CCLS.	USPAT; USOCR	OR	OFF	2006/02/28 11:48
S21	14	("5336638" "5561082").PN. OR ("6207561").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2006/02/28 11:52
S22	100	S17 and (MIM or metal-insulator-metal)	USPAT; USOCR	ADJ	ON	2006/02/28 12:13
S23	60	(spiral or circular) same MIM same capacitor	USPAT; USOCR	ADJ	ON	2006/02/28 12:14
S24	19	("5837578" "6025226" "6069051" "6087261" "6117747" "6143601" "6157793" "6159787" "6242315" "6259128" "6271084" "6271555" "6320244" "6346454" "6399495" "6426249" "6472721" "6498092" "6551919").PN. OR ("6624040").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2006/02/28 13:11
S25	6	("6329234" "6472124").PN. OR ("6670237").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2006/02/28 13:37
S26	7	("5371700" "5576240" "5897371" "5914851" "6083824").PN. OR ("6472124").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2006/02/28 15:04
S27	1	("6624040").PN.	USPAT; USOCR	OR	OFF	2006/02/28 15:05
S28	19	("5837578" "6025226" "6069051" "6087261" "6117747" "6143601" "6157793" "6159787" "6242315" "6259128" "6271084" "6271555" "6320244" "6346454" "6399495" "6426249" "6472721" "6498092" "6551919").PN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2006/02/28 16:19
S29	416	spiral near3 capacitor	US-PGPUB; USPAT; USOCR	ADJ	ON	2006/02/28 16:20
S30	300	spiral near2 capacitor	US-PGPUB; USPAT; USOCR	ADJ	ON	2006/03/01 07:49

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S31	1	("5202655").PN.	USPAT; USOCR	OR	OFF	2006/03/01 07:51
S32	1	("5611008").PN.	USPAT; USOCR	OR	OFF	2006/03/01 07:52
S33	1	("5752182").PN.	USPAT; USOCR	OR	OFF	2006/03/01 07:53
S34	1	("5959515").PN.	USPAT; USOCR	OR	OFF	2006/03/01 07:54
S35	1	("6635561").PN.	USPAT; USOCR	OR	OFF	2006/03/01 08:13
S36	1	("4959705").PN.	USPAT; USOCR	OR	OFF	2006/03/01 08:14
S37	1	("6313003").PN.	USPAT; USOCR	OR	OFF	2006/03/01 08:15
S38	1	("6384442").PN.	USPAT; USOCR	OR	OFF	2006/03/01 08:24
S39	1	("6534374").PN.	USPAT; USOCR	OR	OFF	2006/03/01 08:26
S40	1	("6030265").PN.	USPAT; USOCR	OR	OFF	2006/03/01 08:28
S41	1	("6309922").PN.	USPAT; USOCR	OR	OFF	2006/03/01 08:29
S42	1	("6274502").PN.	USPAT; USOCR	OR	OFF	2006/03/01 08:30
S43	1	("6258652").PN.	USPAT; USOCR	OR	OFF	2006/03/01 09:02
S44	1	("6054329").PN.	USPAT; USOCR	OR	OFF	2006/03/01 08:32
S45	2732	(29/25.41,25.42).CCLS.	USPAT; USOCR	OR	OFF	2006/03/01 09:03
S46	631	S45 and (wafer or substrate or etch or damascene)	USPAT; USOCR	ADJ	ON	2006/03/01 09:05
S47	596	S45 and (wafer or substrate)	USPAT; USOCR	ADJ	ON	2006/03/01 10:15
S48	188	S45 and (wafer or substrate) and mask	USPAT; USOCR	ADJ	ON	2006/03/01 10:17
S49	67	S45 and (wafer or substrate) and mask and (low-k or high-k or dielectric constant)	USPAT; USOCR	ADJ	ON	2006/03/01 10:31
S50	228	spiral with capacitor same (wafer or substrate)	USPAT; USOCR	ADJ	ON	2006/03/01 10:43
S51	1	("6661079").PN.	USPAT; USOCR	OR	OFF	2006/03/01 10:43

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S52	3	("5111169" "6297524" "6383858").PN. OR ("6661079").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2006/03/01 10:44
S53	2	"6717193"	US-PGPUB; USPAT; USOCR	ADJ	ON	2006/03/01 10:44
S54	0	("2004/0219757").URPN.	USPAT	ADJ	ON	2006/03/01 10:45
S55	1	("6717193").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/03/01 10:45
S56	15	("5583359" "5696394" "5700731" "5895239" "5926359" "5939766" "6177305" "6180976" "6200629" "6232197" "6238964" "6251740" "6259128" "6385033" "6479850").PN. OR ("6717193").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2006/03/01 10:48
S57	0	S56 and (low-k and high-k)	US-PGPUB; USPAT; USOCR	ADJ	ON	2006/03/01 10:48
S58	1	S56 and (low-k or high-k)	US-PGPUB; USPAT; USOCR	ADJ	ON	2006/03/01 10:48
S59	7	S56 and dielectric constant	US-PGPUB; USPAT; USOCR	ADJ	ON	2006/03/01 10:51
S60	1	("6479850").PN.	USPAT; USOCR	OR	OFF	2006/03/01 12:34
S61	1910	(361/303,306.3,311-313).CCLS.	USPAT; USOCR	OR	OFF	2006/03/01 12:38
S62	711	S61 and (low-k or high-k or dielectric constant)	USPAT; USOCR	ADJ	ON	2006/03/01 12:39
S63	447	S61 and (low-k or high-k or dielectric constant) and (wafer or substrate)	USPAT; USOCR	ADJ	ON	2006/03/01 12:40
S64	445	S61 and (low-k and high-k or dielectric constant) and (wafer or substrate)	USPAT; USOCR	ADJ	ON	2006/03/01 12:40
S65	9	S61 and (low-k and high-k) and (wafer or substrate)	USPAT; USOCR	ADJ	ON	2006/03/01 12:42
S66	46	S61 and (MIM or metal-insulator-metal) and (wafer or substrate)	USPAT; USOCR	ADJ	ON	2006/03/01 12:41
S67	294	S61 and (low-k and high-k or high dielectric constant or low dielectric constant) and (wafer or substrate)	USPAT; USOCR	ADJ	ON	2006/03/01 12:42

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S68	79	S61 and (low-k and high-k or high dielectric constant and low dielectric constant) and (wafer or substrate)	USPAT; USOCR	ADJ	ON	2006/03/01 12:44
S69	133	low leakage and high breakdown and capacitor	USPAT; USOCR	ADJ	ON	2006/03/01 15:30
S70	39	low leakage same high breakdown same capacitor	USPAT; USOCR	ADJ	ON	2006/03/01 15:30
S71	1910	(361/303,306.3,311-313).CCLS.	USPAT; USOCR	OR	OFF	2006/03/01 15:45
S72	90	S71 and (low-k and high-k or high dielectric and low dielectric) and (wafer or substrate)	USPAT; USOCR	ADJ	ON	2006/03/01 16:23
S73	0	organix low-k dielectric materials	USPAT; USOCR	ADJ	ON	2006/03/01 16:24
S74	155	organic low-k	USPAT; USOCR	ADJ	ON	2006/03/01 16:24
S75	74	organic low-k dielectric	USPAT; USOCR	ADJ	ON	2006/03/01 16:25
S76	0	organic low-k dielectric same capacitor	USPAT; USOCR	ADJ	ON	2006/03/01 16:25
S77	0	organic low-k dielectric andcapacitor	USPAT; USOCR	ADJ	ON	2006/03/01 16:25
S78	15	organic low-k dielectric and capacitor	USPAT; USOCR	ADJ	ON	2006/03/01 16:50
S79	8	Ta/TaN same capacitor	USPAT; USOCR	ADJ	ON	2006/03/01 16:54
S80	8	"Ta/TaN" same capacitor	USPAT; USOCR	ADJ	ON	2006/03/01 16:54